

Degradation of LaMnO_{3-y} surface layer in LaMnO_3 /metal interface

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We report electrical measurements showing the degradation processes of LaMnO_{3-y} (LaMnO) in LaMnO /normal metal interface in both point contact and planar-type junctions. Immediately after the preparation of the interface, the degradation process was followed by measuring the evolution of the junction resistance versus time. This process is characterized by the appearance of a second maximum in the resistance vs. temperature (R - T) dependence at temperatures lower than the Curie temperature T_c , at which the metal-insulator transition occurs in the bulk. These effects are explained in terms of the formation of a depleted interface layer in LaMnO caused by an out-diffusion of oxygen from the manganite surface to the normal metal. This assumption is confirmed by XPS measurement. Similar results on LaSrMnO_{3-y} interfaces are also obtained.

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The magnetoresistive rare earth perovskites $\text{La}_{1-x}\text{A}_x\text{MnO}_{3-y}$ (LaAMnO , $\text{A} = \text{Ca}, \text{Sr}, \text{Pb}$), which include LaMnO , have been in the research spotlight for a decade. Optimally doped LaAMnO exhibits a paramagnetic-insulating behavior above the Curie temperature T_c and a ferromagnetic-metallic behavior below T_c . In the recent years, the giant magnetoresistance phenomenon (MR) has been intensively studied in these materials. However till low-field, MR effects in granular

ins and tunneling of spin-polarized electrons through an insulating barrier in LaAMnO /Insulator/ LaAMnO magnetic tunnel junctions (MTJ) gave promise to their technological applications like magnetic field sensor and nonvolatile magnetic random access memory. One can expect a near 100% value of tunneling magnetoresistance (TMR) in tunnel junctions based on half-metallic LaAMnO ferromagnet. TMR depends on the quality of the magnetic state of the LaAMnO surface, interface quality, surface roughness of the electrodes, etc. A non-linear tunneling behavior observed in MTJ could be explained by extrinsic factors playing a dominant role in the MTJ interfaces. This assumption has been made by several authors. Park et al.¹ showed that even in a fully oxidized LaSrMnO sample, the magnetic properties at the

surface boundary are significantly different from those of the bulk. In addition, several experiments indicated the creation of an oxygen depleted layer of LaAMnO interfaces. M. Ieville et al.² studied the interface resistance and transport across conducting ferromagnetic oxide/metal interfaces. They measured a very high resistance of $\text{LaSrMnO}/\text{Al}(\text{Nb})$ junctions, which could be explained by the existence of a degraded surface layer of ferromagnetic oxide due to a loss of oxygen. Also de Teresa et al.³ observed a dependence of TMR on the type of tunneling barrier. The present work was stimulated by the above mentioned results, but mainly by the results published in our previous paper⁴. $\text{LaMnO}/\text{Al}_2\text{O}_3/\text{Nb}$ junctions were fabricated for the study of the influence of illumination on the electrical properties of MTJ. The Al_2O_3 insulating barrier was prepared using well-known thin film Nb technology⁵: An aluminum thin film was sputtered on LaMnO , and then oxidized in an oxygen atmosphere. Finally a semi-transparent Nb upper electrode was sputtered on the top. Using the same technique with the same preparation parameters, the width of the barrier created on the LaMnO was about two times higher than that for $\text{Nb}/\text{Al}_2\text{O}_3/\text{Nb}$ junctions.

In this paper we study the LaMnO surface properties in contact with Al, In, Au and Pb metals in order to explain the physical processes in the interface which give rise to an unusual behavior of MTJ. The LaMnO /normal metal point contact exhibits a change of resistance immediately after its preparation. In the planar junctions (more stable than point contact) the appearance of a second maximum in the R - T dependence was observed several hours after junction preparation. These effects are explained by an out-diffusion of oxygen from LaMnO , and they were confirmed by XPS spectroscopy.

200 nm thick LaMnO epitaxial thin film with $T_c = 270$ K were deposited on single crystalline SrTiO_3 substrates by low pressure liquid source metal-organic chemical vapour deposition (MOCVD)⁶. LaMnO /metal point contacts were realized using a holder which exerted a constant pressure of the tip onto the sample. Bulk Au, Al, or Pb were used for the upper electrode. The shape

of the sharp point was prepared by mechanical sharpening. After the electrical measurements, a $200 \times 200 \text{ nm}^2$ geometric area was evaluated for the Pb tip.

For the preparation of planar junctions, a 40 nm -wide and 260 nm -long LaMnO_3 base electrode was formed by wet etching through resist mask. After stripping the photoresist, the area for deposition of next layers by lift-off technique was defined in positive photoresist. Shortly before the deposition of the barrier and the upper electrodes, the surface of LaMnO_3 was etched to eliminate a contaminated and degraded upper layer. A 100 nm thick Al or In layer was deposited by thermal evaporation. Junctions with an area of $40 \times 40 \text{ nm}^2$ were realized after the removal of the photoresist.

The R-T and resistance vs. time (R-t) characteristics were measured by a computer controlled four point method.

XPS spectra were obtained in an ESCALAB 210 spectrometer that consisted of two separate independently-pumped chambers. Pressures in the range of $6 \times 10^{-11} \text{ mbar}$ and 10^{-8} mbar were obtained in the analysis and preparation chambers, respectively. Al has been evaporated in the analysis chamber from a resistively heated filament made of Al wire wrapped around a thick tungsten wire. The power was maintained to give a reproducible evaporation rate of 1 monolayer of Al per minute. Control evaporation carried out onto a clean Au foil showed that under our experimental conditions, only metallic Al is evaporated, maintaining this oxidation state throughout all the acquisition time. A hemispherical electron energy analyser working in the pass energy constant mode at a value of 50 eV was used. Ultramonochromatized Al K α radiation was used as the excitation source. Spectra were energy-calibrated by taking the $\text{La}3d_{5/2}$ peak at 834.6 eV (BE). The spectra were acquired at 90° (normal) and 20° (grazing) degrees with respect to sample surface.

In Fig 1, the LaMnO_3 /metal point contact resistance dependence versus time shows a significant increase at several hundred seconds after the preparation of the contact. These changes were observed even if noble metal (Au) was used as the upper electrode material. Similar results on high- T_c superconductors (HTS) were described in our previous work⁷. The change of the point contact resistance was explained within an oxygen out-diffusion model.

The total point contact resistance with a tip made of nonreactive metal (e.g. Au) can be expressed as $R = R_M + R_{\text{LaMnO}_3} + R_T$, where R_T is the tunneling resistance and R_M and R_{LaMnO_3} the contact resistances with metal and LaMnO_3 , respectively. We suppose that R_M and R_T are constant in time for stable nonreactive metals, and the change of resistance R is then given by the change of R_{LaMnO_3} . The creation of additional barriers from a LaMnO_3 oxygen depleted layer as well as from the oxide of the upper metallic electrode (created from reactive metal like Al, Pb) creates a complex interface. But in all cases, the Curie temperature T_c in the LaMnO_3 oxygen depleted region must be changed also.

In the next measurements the planar junctions were used because they were more stable than the point contact ones. Because Al is a very reactive metal with a very short time of interaction, indium as an upper electrode was used for the following measurement. The R-T characteristic measured on a LaMnO_3/In planar junction at different times (3, 5 and 23 hours) after preparation of the contacts is shown in Fig 2. We observed the classical maximum correlated with the I-M transition of the bulk material at T_c around 275 K of the bulk material. This maximum did not change very much with time. It means that the oxygen content in the bulk material does not change. After a long time (23 hours) a second maximum appears around $T'_c = 185 \text{ K}$ in the R-T characteristics. We know that in LaMnO_3 systems the T_c decreases with a decrease of the oxygen content, and it disappears for deoxygenated samples that exhibit semiconducting properties. This new maximum is related to the oxygen depleted interface, and it is broader due to a distribution of T'_c . This value of $T'_c = 185 \text{ K}$ corresponds to an average oxygen content at the interface of y around 0.1 .⁸

To confirm the occurrence of out-diffusion processes in the LaMnO_3 surface layer, XPS measurements of LaMnO_3/Al interfaces were studied. Fig.3 shows spectra of the O 1s, Mn 2p, Al 2p and La 3d regions measured on clean (original) LaMnO_3 surface (curves a) at the normal acquisition angle, after the deposition of around 1 monolayer of Al (curves b), at the normal acquisition angle, around 2 monolayers of Al, at the normal acquisition angle (curves c), and curves d were measured as curves c at a grazing acquisition angle. One can see the following features in the XPS spectra after the deposition of Al:

- two peaks correlated with Al and Al_2O_3 ,
- two peaks in the O 1s spectra correlated with oxygen bonding in LaMnO_3 at 529.9 eV and Al_2O_3 at 531.6 eV ,
- shift of the peaks in the Mn 2p spectra due to the decreasing of Mn valency.

The deposition of the first monolayer of Al on the LaMnO_3 surface provokes the oxidation of Al to Al^{3+} , whose peak arises at about 75 eV (BE). This behaviour was tested by a simultaneous deposition of Al on Au. The detection of metallic Al during the whole experiment (more than 1 hour) excludes the oxidation of Al due to the residual O_2 partial pressure in the analytic chamber. In addition, when a second amount of Al was deposited (curve c in Fig.3a), most of it remained metallic (peak at 72.6 eV BE). Finally, when this situation is examined at the grazing acquisition angle (curve d in Fig.3a), the relative intensity of the peak from Al(0), in comparison with that from Al^{3+} , increases substantially, indicating that metallic Al is located on the top of the Al_2O_3 .

The oxidation of Al in the LaMnO_3/Al interface accompanying the appearance of two peaks in the O 1s spectra is correlated with a change of binding energy due to the creation of Al_2O_3 . The smooth second peak was measured also on clean LaMnO_3 surface (curve a in Fig.3c) as well as after cleaning treatment. The origin of the second peak can be explained by the contamination of LaMnO_3

by CO_3^- species within the preparation procedure of the LaMnO thin film. Anyway, the intensity of the peak at the energy of 520.6 eV increase after the deposition of Al (curves b and c in Fig.3c) due to the arising of O^{2-} ions in Al_2O_3 . The measurement at the grazing angle shows that Al_2O_3 is created on the LaMnO surface (the global intensity of Al 2p signal grows and the Mn and La signals decrease). These facts also indicate the existence of metallic Al on the top of Al_2O_3 .

A significant chemical shift of Mn 2p peak from 642.5 eV before Al evaporation to 641.4 eV after Al evaporation strongly indicates a decrease of Mn valency to +3 state with a subsequent change of the $\text{Mn}^{3+}/\text{Mn}^{4+}$ ratio, typical for oxygen-deficient LaMnO .

From XPS measurements described above, we can confirm the loss of oxygen from the LaMnO in the LaMnO/Al interface and the creation of a $\text{LaMnO}/\text{Al}_2\text{O}_3/\text{Al}$ junction with a subsequent change in the $\text{Mn}^{3+}/\text{Mn}^{4+}$ ratio.

In conclusion, we presented R-T and R-t measurements on $\text{LaMnO}/\text{metal}$ point contact and planar junctions. The time evolution of point contact junction resistance as well as arising of a second peak on the R-T characteristics were observed. These effects were explained in terms of the formation of a depleted interface layer in LaMnO_{3-x} caused by the out-diffusion of oxygen from the manganese surface to the normal metal. This assumption was confirmed by XPS measurements. The similar results (XPS as well as time evolution of point contact resistance) on LaSrMnO magnetoresistive thin films were also obtained.

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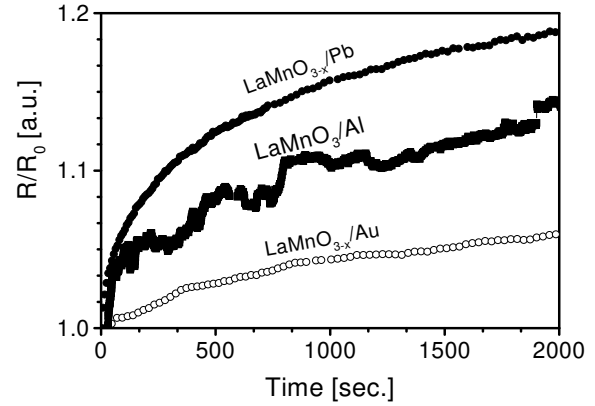


FIG. 1. Time evolution of the $\text{LaMnO}/\text{metal}$ (Au - open circles, Al - solid squares and Pb - solid circles) point contact resistance. The measurement was started immediately after the point contact preparation.

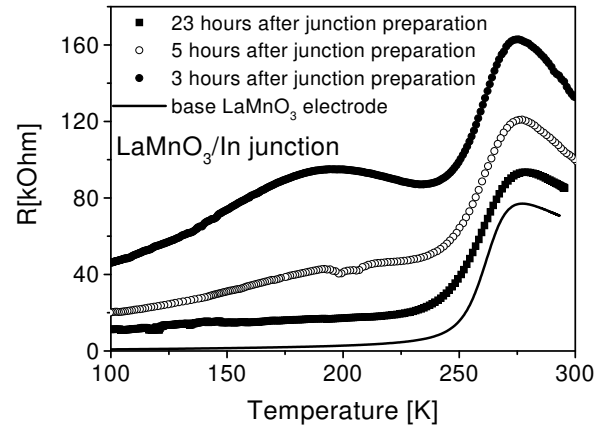


FIG. 2. R-T dependence of the LaMnO electrode (solid line) and R_T -T dependence of LaMnO/In planar junction measured 3 hours (solid squares), 5 hours (open circles) and 23 hours (solid circles) after the deposition of the In upper electrode.

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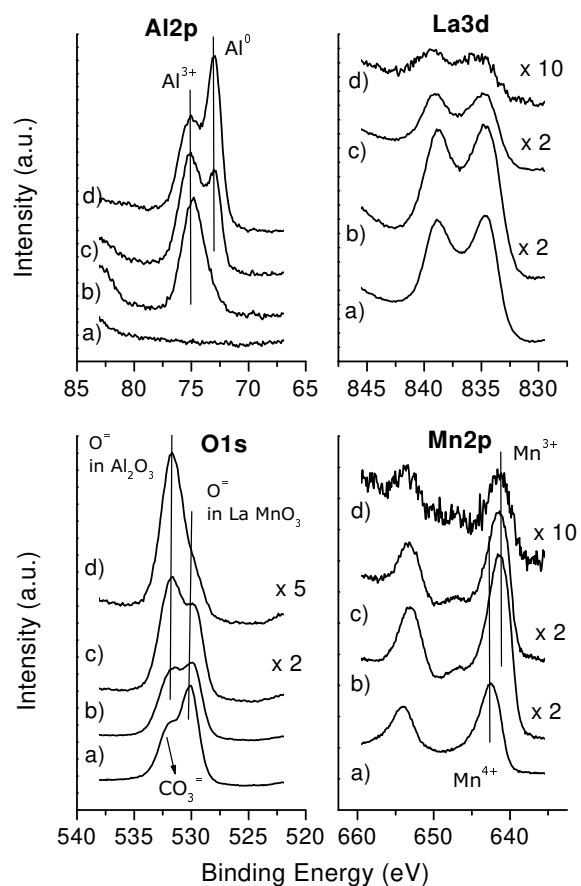


FIG. 3.

XPS spectra of the O 1s, Mn 2p, Al 2p and La 3d regions measured on the clean surface of LaMnO_3 (curves a) after the deposition of one monolayer and two monolayers of Al, at the normal acquisition angle (curves b and c, respectively) and the same that curves c, at the grazing acquisition angle.